

UTC UNISONIC TECHNOLOGIES CO., LTD

UT9564

Power MOSFET

-40V, -7.3A P-CHANNEL **ENHANCEMENT MODE POWER** MOSFET

DESCRIPTION

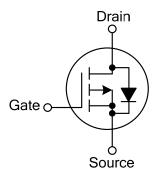
The UTC UT9564 is a P-ch enhancement mode power MOSFET and it uses UTC perfect technology to provide customers with fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The UTC UT9564 is ideal for applications such as low voltage applications, DC/DC converters and all commercial-industrial surface mount applications.

FEATURES

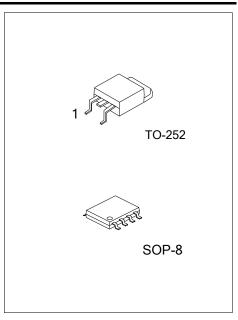
- * Simple Drive Requirement
- * Fast Switching Speed
- * Low On-Resistance

SYMBOL



ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment								Dealing	
Lead Free Halogen Free		Package	1	2	3	4	5	6	7	8	Packing	
UT9564L-TN3-R	UT9564G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel	
-	UT9564G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel	
Note: Pin Assignment: G: Gate D: Drain S: Source												
Note: Pin Assignment: G: Gate D: Drain S: Source		(1) T: Tubo (2) TN3: T (3) L: Leac	0-2!	52, S	808:	SOF		ree a	and I	Lead	1 Free	



UT9564

■ MARKING

TO-252	SOP-8				
UTC UT9564□ C: Lead Free G: Halogen Free Data Code	8 7 6 5 UTC □□□□ UT9564G • • • • • • Lot Code 1 2 3 4				



ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _{GS}	±25	V
Continuous Drain Current (Note 2)	T _A =25°C	I _D	-7.3	А
	T _A =70°C		-5.9	Α
Pulsed Drain Current (Note 1)		I _{DM}	-30	Α
Power Dissipation (T _A =25°C)	TO-252	PD	2	14/
	SOP-8		2.5	W
Linear Derating Factor	•		0.02	W/°C
Junction Temperature		TJ	-55 ~150	°C
Storage Temperature		T _{STG}	-55 ~150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient (Note 2)	TO-252	0	62.5	°C/W
	SOP-8	θ_{JA}	50	C/W

Notes: 1. Pulse width limited by Max. junction temperature. 2. Surface mounted on 1 in² copper pad of FR4 board, t ≤10sec; 125°C /W when mounted on Min. copper pad.

ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

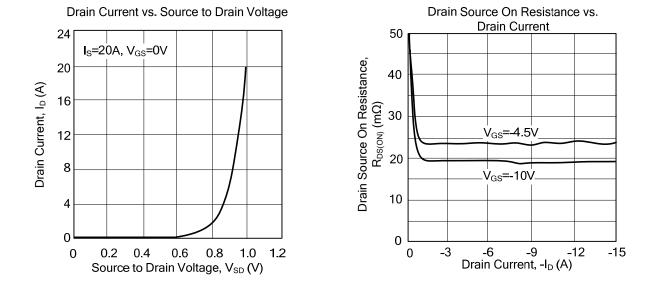
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS	_		_		_				
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =-250μΑ, V _{GS} =0V	-40			V			
Breakdown Voltage Temperature Coefficient	$\triangle BV_{DSS} / \triangle T_J$	Reference to 25°C, I _D =-1mA		-0.03		V/°C			
Drain-Source Leakage Current	I	V _{DS} =-40V, V _{GS} =0V, T _J =25°C			-1	μA			
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-32V, V _{GS} =0V, T _J =70°C			-25	μΑ			
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±25V			±100	nA			
ON CHARACTERISTICS									
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250µA	-1		-3	V			
Static Drain-Source On-State Resistance	P	V _{GS} =-10V, I _D =-7A			28	mΩ			
(Note)	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-5A			40	11152			
Forward Transconductance	g fs	V _{DS} =-10V, I _D =-7A		13		S			
DYNAMIC PARAMETERS									
Input Capacitance	C _{ISS}	−V _{GS} =0V, V _{DS} =-25V, −f=1.0MHz		2240	3600	рF			
Output Capacitance	Coss			300		рF			
Reverse Transfer Capacitance	C _{RSS}			250		рF			
SWITCHING PARAMETERS									
Total Gate Charge (Note)	Q_{G}	V _{GS} =-4.5V, V _{DS} =-32V, I _D =-7A		27	43	nC			
Gate to Source Charge	Q_{GS}			6		nC			
Gate to Drain Charge	Q_{GD}			14		nC			
Turn-ON Delay Time (Note)	t _{D(ON)}			14		ns			
Rise Time	t _R	V _{GS} =-10V, V _{DS} =-20V, I _D =-1A,		8		ns			
Turn-OFF Delay Time	t _{D(OFF)}	R_G =3.3 Ω , R_D =20 Ω		46		ns			
Fall-Time	t⊧			17		ns			
SOURCE- DRAIN DIODE RATINGS AND CI	HARACTERIS	<u>FICS</u>							
Maximum Body-Diode Continuous Current	ls				-7.3	Α			
Maximum Body-Diode Pulsed Current	I _{SM}				-30	Α			
Drain-Source Diode Forward Voltage (Note)	V _{SD}	I _S =-2A, V _{GS} =0V			-1.2	V			
Reverse Recovery Time (Note)	t _{RR}	I _S =-7A, V _{GS} =0V,		144		ns			
Reverse Recovery Charge	Q _{RR}	dl/dt=100A/µs		110		nC			
Note: Pulse width \leq 300µs, duty cycle \leq 2%.									

e width ≤ 300µs, duty cycle ≤ 2%.



UT9564

TYPICAL CHARACTERISTICS



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